



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

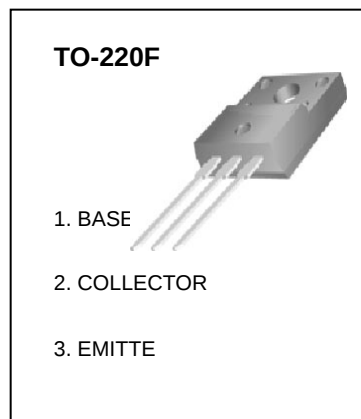
TO-220F Plastic-Encapsulate Transistors

3CA1837 TRANSISTOR (PNP)

FEATURES

- High Transition Frequency : $f_T=70\text{MHz(Typ)}$
- Complementary to 3DA4793
- Collector Power Dissipation

$P_{CM} : 2\text{W (Tamb=25}^\circ\text{C)}$
 $20\text{ W (Tcase=25}^\circ\text{C)}$



MAXIMUM RATINGS* $T_A=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	-230	V
V_{CEO}	Collector-Emitter Voltage	-230	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current -Continuous	-1000	mA
I_B	Base Current	-100	mA
T_J	Junction Junction	150	$^\circ\text{C}$
T_{stg}	Storage Junction	-55-150	$^\circ\text{C}$

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

ELECTRICAL CHARACTERISTICS ($T_{amb}=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-100\mu\text{A}$, $I_E=0$	-230			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-1\text{mA}$, $I_B=0$	-230			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-100\mu\text{A}$, $I_C=0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB}=-230\text{V}$, $I_E=0$			-10	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=-5\text{V}$, $I_C=0$			-10	μA
DC current gain	h_{FE}	$V_{CE}=-5\text{V}$, $I_C=-100\text{mA}$	100		320	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-500\text{mA}$, $I_B=-50\text{mA}$			-1.5	V
Transition frequency	f_T	$V_{CE}=-10\text{V}$, $I_C=-100\text{mA}$	30			MHz

Typical Characteristics

3CA1837

